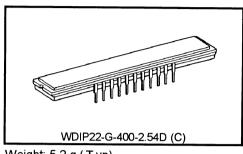
TENTATIVE

TOSHIBA CCD Linear Image Sensor CCD (Charge Coupled Device)

TCD1711DG

The TCD1711DG is a high sensitive and low dark current 7450 elements CCD image sensor.

The sensor is designed for facsimile, imagescanner and OCR. The device contains a row of 7450 elements photodiodes which provide a 24 lines / mm (600DPI) across a A3 size paper. The device is operated by 5 V (pulse), and 10 V power supply.



Weight: 5.2 g (Typ)

FEATURES

• Number of Image Sensing Elements: 7450 elements

Image Sensing Element Size

: $4.7 \,\mu m$ by $4.7 \,\mu m$ on $4.7 \,\mu m$ centers

Photo Sensing Region : High sensitive and low voltage dark signal pn photodiode

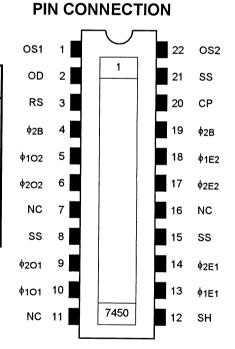
• Clock : 2 phase (5 V)

• Package : 22 pin CERDIP package

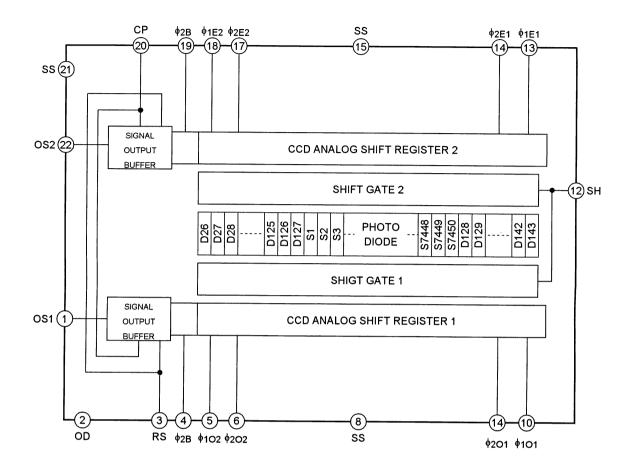
MAXIMUM RATINGS (Note 1)

			,
CAHRACTERISTIC	SYMBOL	RATING	UNIT
Clock Pulse Voltage	V_{ϕ}		V
Shift Pulse Voltage	V _{SH}	-0.3~8	
Reset Pulse Voltage	V _{RS}	-0.5~0	
Clamp Pulse Voltage	V _{CP}		
Power Supply Voltage	V _{OD}	-0.3~15	V
Operating Temperature	T _{opr}	0~60	°C
Storage Temperature	T _{stg}	-25~85	°C

Note 1: All voltage are with respect to SS terminals (Ground).



CIRCUIT DIAGRAM



PIN NEMES

φ1E, O	Clock (Phase 1)
φ2E, O	Clock (Phase 2)
ф2В	Final Stage Clock (Phase 2)
SH	Shift Gate
RS	Reset Gate
СР	Clamp Gate
OS1	Signal Output 1
OS2	Signal Output 2
OD	Power
SS	Ground
NC	Non Connection

OPTICAL / ELECTRICAL CHARACTERISTICS

(Ta = 25°C, V_{OD} = 10 V, V_{φ} = V_{SH} = V_{RS} = V_{CP} = 5 V (パルス), f_{φ} = 1 MHz, t_{INT} (INTEGRATION TIME) = 10 ms, LIGHT SOURCE = DAYLIGHT FLUORESCENT LAMP, LOAD RESISTANCE-100kΩ)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Sensitivity	R	12	15	18	V/lx·s	
Photo Response Non Uniformity	PRNU	_	4	10	%	(Note2)
	PRNU (3)		6	12	mV	(Note8)
Saturation Output Voltage	V _{SAT}	1.5	1.8	_	V	(Note3)
Saturation Exposure	SE	0.08	0.12		lx·s	(Note4)
Dark Signal Voltage	V _{DRK}	_	1.0	3	mV	(Note5)
Dark Signal Non Uniformity	DSNU	_	4.0	10	mV	(Note5)
DC Power Dissipation	PD		250	375	mW	
Total Transfer Efficiency	TTE	92	98		%	
Output Impedance	ZO		0.2	1	kΩ	
Dynamic Range	DR	_	1800	_		(Note6)
DC Signal Output Voltage	Vos1	3.0	4.5	6.0	V (41.1.7
	V _{OS2}	3.0	4.5	6.0		(Note7)
DC Differential Error Voltage	V _{OS1} - V _{OS2}		_	300	mV	
Random Noise	N _{Dσ}	_	1.0	_	mV	(Note9)

Note 2: Measured at 50% of SE (Typ.)

Definition of PRNU : PRNU = $\frac{\Delta \chi}{\overline{\chi}} \times 100(\%)$

Where $\overline{\chi}$ is average of total signal outputs and $\Delta \chi$ is maximum deviation from $\overline{\chi}$ under uniform illumination. (Channel 1)

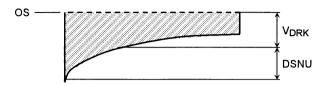
In the case of 3725 elements (Channel 2), the condition is the same as above too.

Note 3: V_{SAT} is defined as minimum saturation output voltage of all effective pixels.

Note 4: Definition of SE : SE = $\frac{V_{SAT}}{R}$ (lx·s)

Note 5: V_{DRK} is defined as average dark signal voltage of all effective pixels.

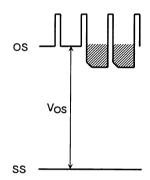
DSNU is defined as different voltage between VDRK and VMDK when VMDK is maximum dark signal voltage.



Note 6: Definition of DR : DR = $\frac{V_{SAT}}{V_{DRK}}$

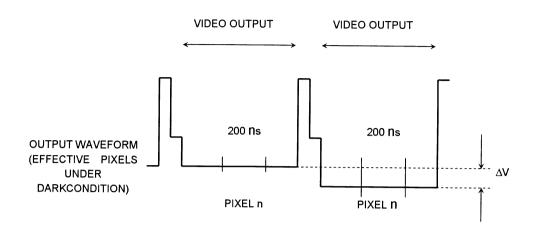
 V_{DRK} is proportional to t_{INT} (Integration Time). So the shorter t_{INT} condition makes wider DR values.

Note 7: DC signal output voltage and DC compensation output voltage are defined as follows:



Note 8: PRNU (3) is defined as maximum voltage with next pixel, where measured 5% of SE (Typ.)

Note 9: Random noise is defined as the standard deviation (sigma) of the output level difference between two djacent effective pixels under no illumination (i.e. dark condition) calculated by the following procedure.



- 1) Two adjacent pixels (pixel n and n + 1) in one reading are fixed as measurement points.
- 2) Each of the output levels at video output periods averaged over 200 nanosecond period to get Vn and Vn + 1.
- 3) Vn + 1 is subtracted from Vn to get ΔV .

$$\Delta V = Vn - Vn + 1$$

4) The standard deviation of ΔV is calculated after procedure 2) and 3) are repeated 30 times (30 readings).

$$\overline{\Delta V} = \frac{1}{30} \sum_{i=1}^{30} \left| \Delta V i \right| \quad \sigma = \sqrt{\frac{1}{30} \sum_{i=1}^{30} \left(\! \left| \Delta V i \right| - \overline{\Delta V} \right)^2}$$

5) Procedure 2), 3) and 4) are repeated 10 times to get 10 sigma values.

$$\overline{\sigma} = \frac{1}{10} \sum_{j=1}^{10} \sigma_j$$

6) $\overline{\sigma}$ value calculated using the above procedure is observed $\sqrt{2}$ times larger than that measured relative to the ground level. So we specify the random noise as follows.

Random noise =
$$\frac{1}{\sqrt{2}}\overline{\sigma}$$

OPERATING CONDTION

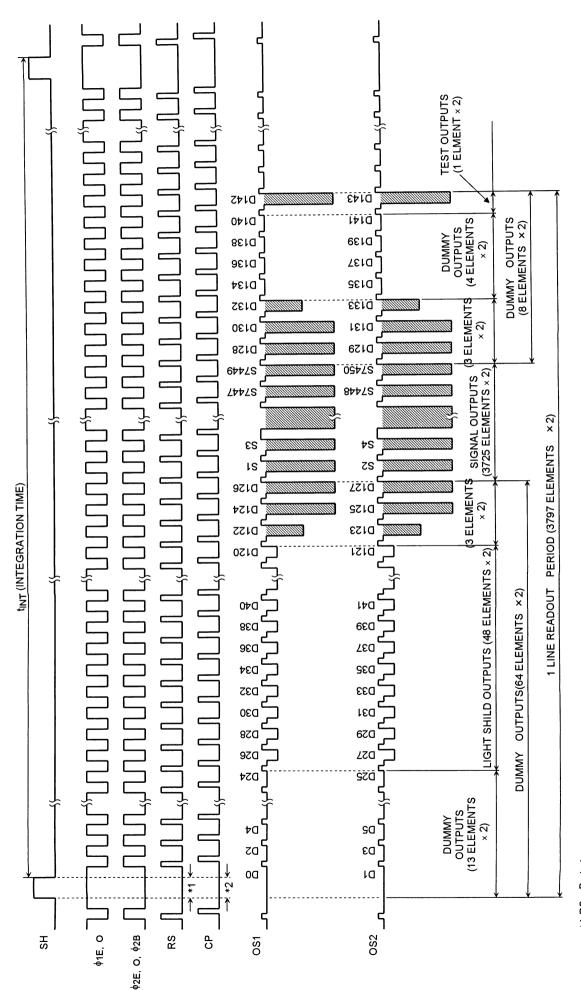
CHARACTERISTIC		SYMBOL	MIN	TYP	MAX	UNIT
Clock Pulse Voltage	"H" Level	V _{ф1E, O}	4.5	5	5.5	V
	"L" Level	V _{φ2E} , O	0		0.5	
Final Stage Clock Voltage	"H" Level	Vion	4.5	5	5.5	V
- mar clage clock voltage	"L" Level	− V _{φ2B}	0	_	0.5	
Shift Pulse Voltage	"H" Level	VsH	4.5	5	5.5	٧
	"L"Level		0	_	0.5	
Reset Pulse Voltage	"H" Level	V _{RS}	4.5	5	5.5	V
	"L" Level		0		0.5	, '
Clamp Pulse Voltage	"H" Level	V _{CP}	4.5	5	5.5	٧
	"L" Level		0	_	0.5	
Power Supply Voltage		V _{OD}	9.5	10	11	٧

CLOCK CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Clock Pulse Frequency	fφ		1	30	MHz
Reset Pulse Frequency	fRS	_	1	30	MHz
Clock Capacitance	C _{φE}		70	_	pF
	C _{¢O}	_	70	_	
Final Stage Clock Capacitance	СфВ	_	10	_	рF
Shift Gate Capacitance	C _{SH}	_	20		pF
Reset Gate Capacitance	C _{RS}		10	_	рF
Clamp Gate Capacitance	C _{CP}	_	10		pF

Note10: $V_{OD} = 10 \text{ V}$

TIMING CHART



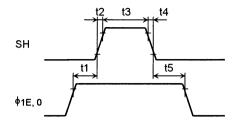
Period *1 RS *2 CP

Period

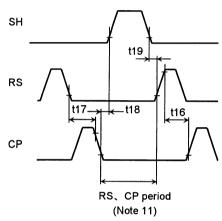
2004-01-30

TIMING REQUIREMENTS

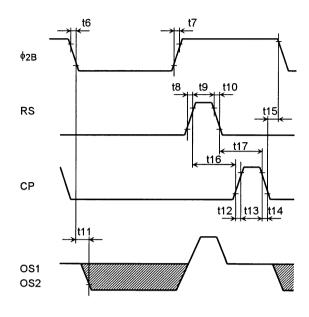
SH、 \$1 Timing



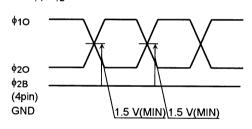
SH、RS、CP Timing

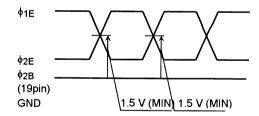


 ϕ_2 , RS, CP, OS Timing



φ₁、φ₂ CROSS POINT





Note 11: Each RS and CP pins put to Low level during this period.

CHARACTERISTIC	SYMBOL	MIN.	TYP. (Note 12)	MAX.	UNIT
Pulse Timing of SH and $_{\phi}$ 1E, $_{\phi}$ 1O	t1, t5	200	500	_	ns
SH Pulse Rise Time, Fall Time	t2, t4	0	50	_	ns
SH Pulse Width	t3	1000	1500	1	ns
φ2B Pulse Rise Time, Fall Time	t6, t7	0	100		ns
RS Pulse Rise Time, Fall Time	t8, t10	0	20		ns
RS Pulse Width	t9	8	100		ns
Video Data Delay Time (Note 13)	t11	_	8	_	ns
CP Pulse Rise Time, Fall Time	t12, t14	0	20	_	ns
CP Pulse Width	t13	8	100	_	ns
Pulse Timing of _φ 2B and CP	t15	0	50		ns
Pulse Timing of RS and CP	t16	0	100		ns
	t17	8	100		ns
Pulse Timing of SH and CP	t18	200	_	_	ns
Pulse Timing of SH and RS	t19	200	_	_	ns

Note 12: TYP. is the case of $f_{RS} = 1.0 \text{ MHz}$

Note 13: TLoad Resistance is 100 $k\Omega$

CAUTION

1. Window Glass

The dust and stain on the glass window of the package degrade optical performance of CCD sensor.

Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

2. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown.

CCD Image Sensor is protected against static electricity, but interior puncture mode device due to static electricity is sometimes detected. In handing the device, it is necessary to execute the following static electricity preventive measures, in order to prevent the trouble rate increase of the manufacturing system due to static electricity.

- a. Prevent the generation of static electricity due to friction by making the work with bare hands or by putting on cotton gloves and non-charging working clothes.
- b. Discharge the static electricity by providing earth plate or earth wire on the floor, door or stand of the work room.
- c. Ground the tools such as soldering iron, radio cutting pliers of or pincer.
 It is not necessarily required to execute all precaution items for static electricity.
 It is all right to mitigate the precautions by confirming that the trouble rate within the prescribed range.

3. Incident Light

CCD sensor is sensitive to infrared light. Note that infrared light component degrades resolution and PRNU of CCD sensor.

4. Lead Frame Forming

Since this package is not strong against mechanical stress, you should not reform the lead frame. We recommend to use a IC-inserter when you assemble to PCB.

5. Soldering

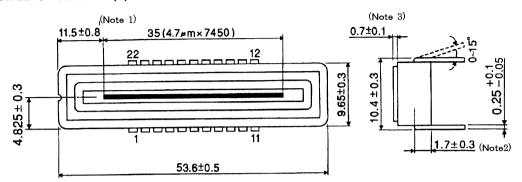
Soldering by the solder flow method cannot be guaranteed because this method may have deleterious effects on prevention of window glass soiling and heat resistance.

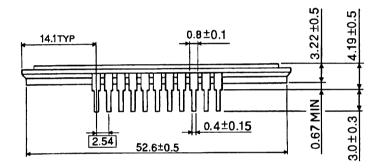
Using a soldering iron, complete soldering within ten seconds for lead temperatures of up to 260°C, or within three seconds for lead temperatures of up to 350°C.

PACKAGE DIMENSIONS

WDIP22-G-400-2.54D (C)

Unit: mm





Note 1: No.1 SENSOR ELEMENT (S1) TO EDGE OF PACKAGE.

Note 2: TOP OF CHIP TO BOTTOM OF PACKAGE.

Note 3: GLASS THICKNESS (n=1.5)

Weight: 5.2g (Typ.)

RESTRICTIONS ON PRODUCT USE

000707EBA

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